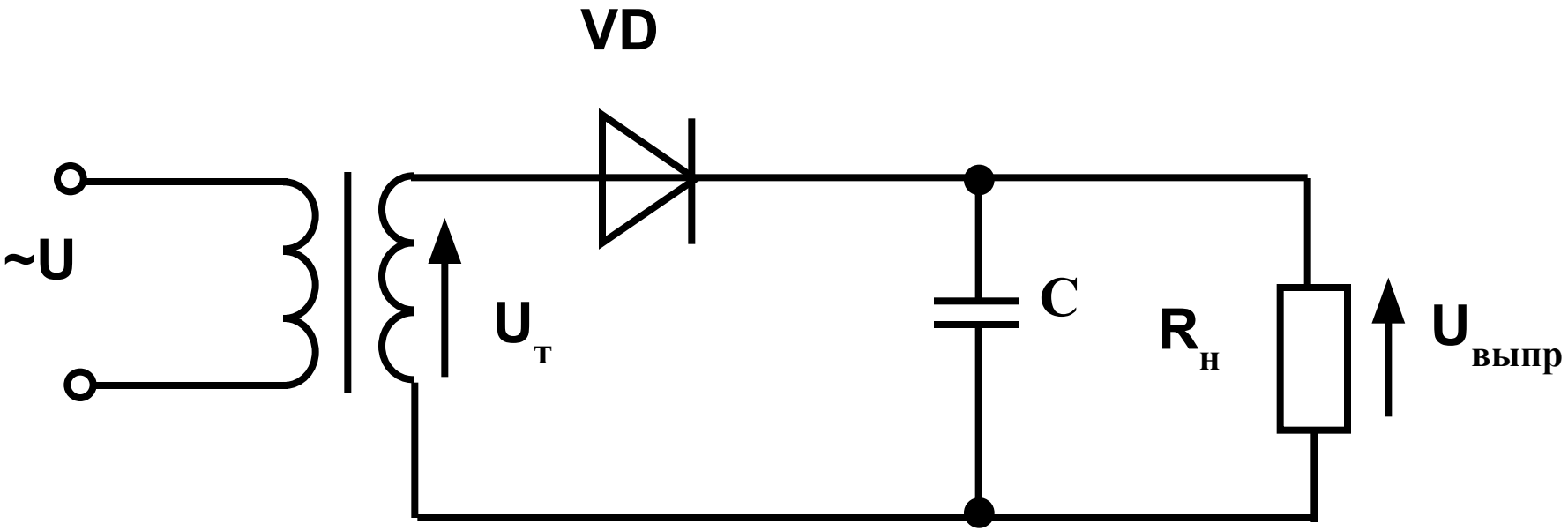
Лекция № 3.1.

Устройство и принцип действия полупроводниковых диодов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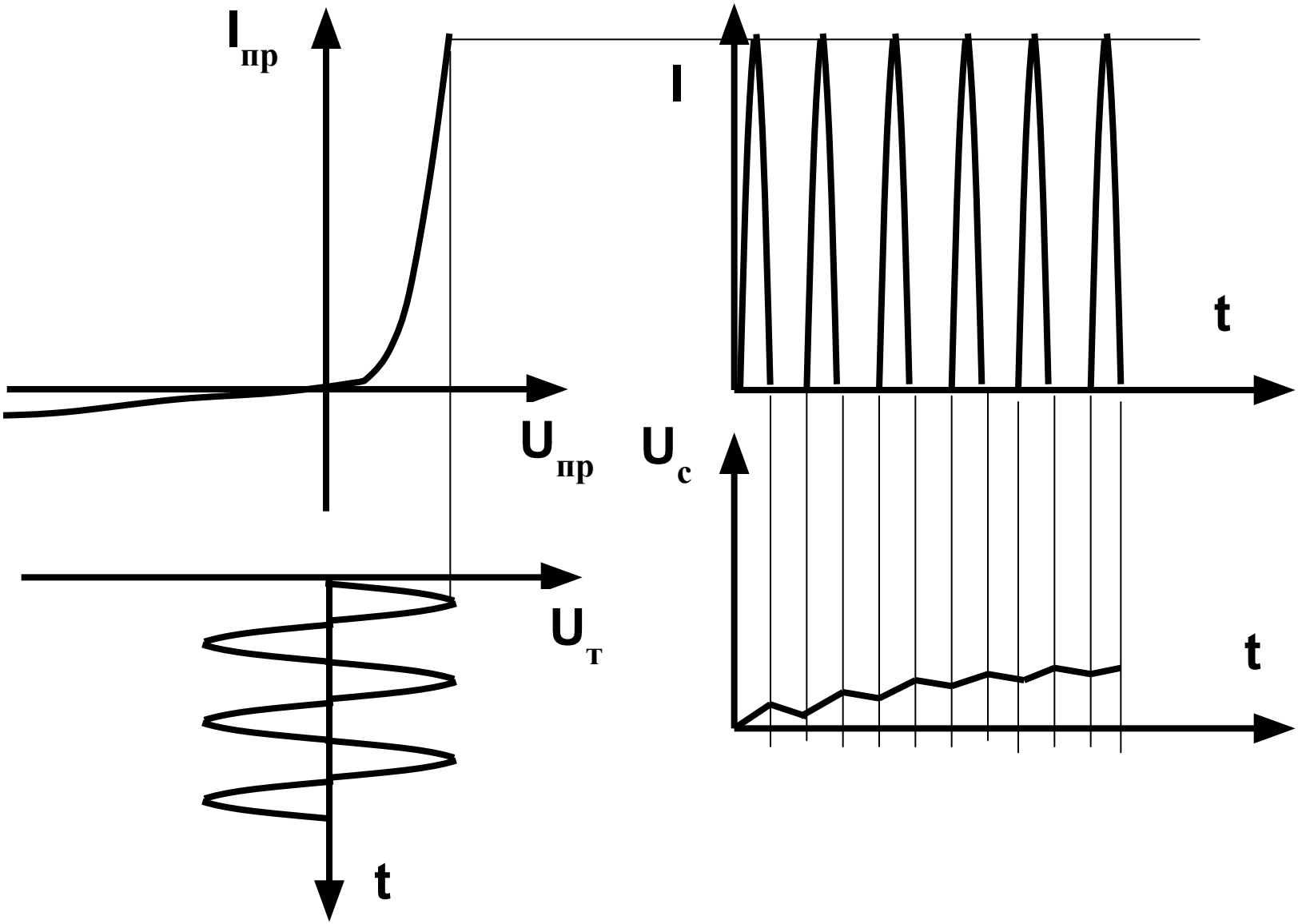
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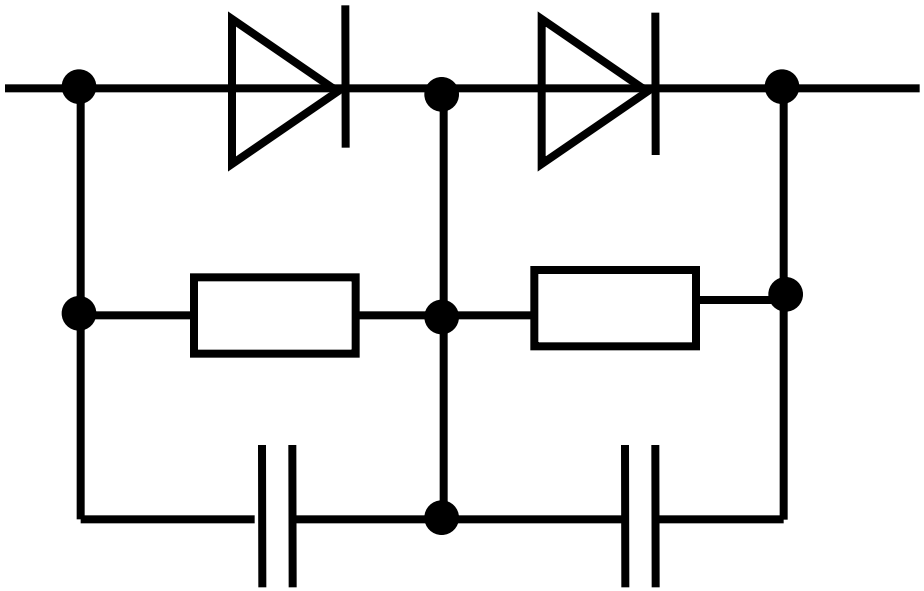

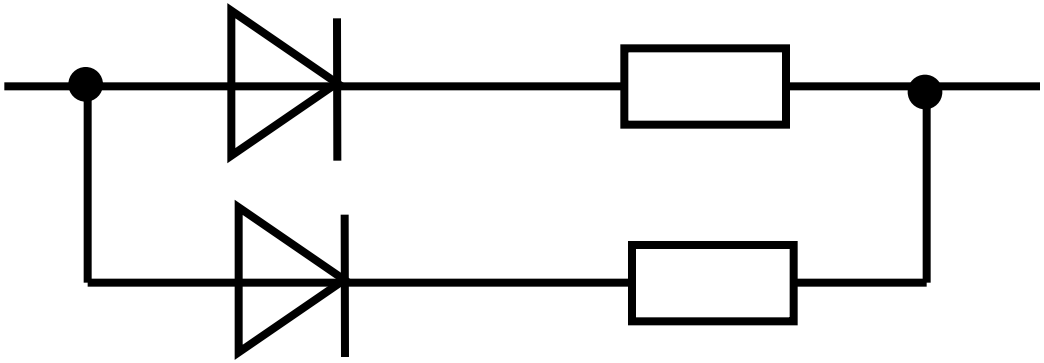

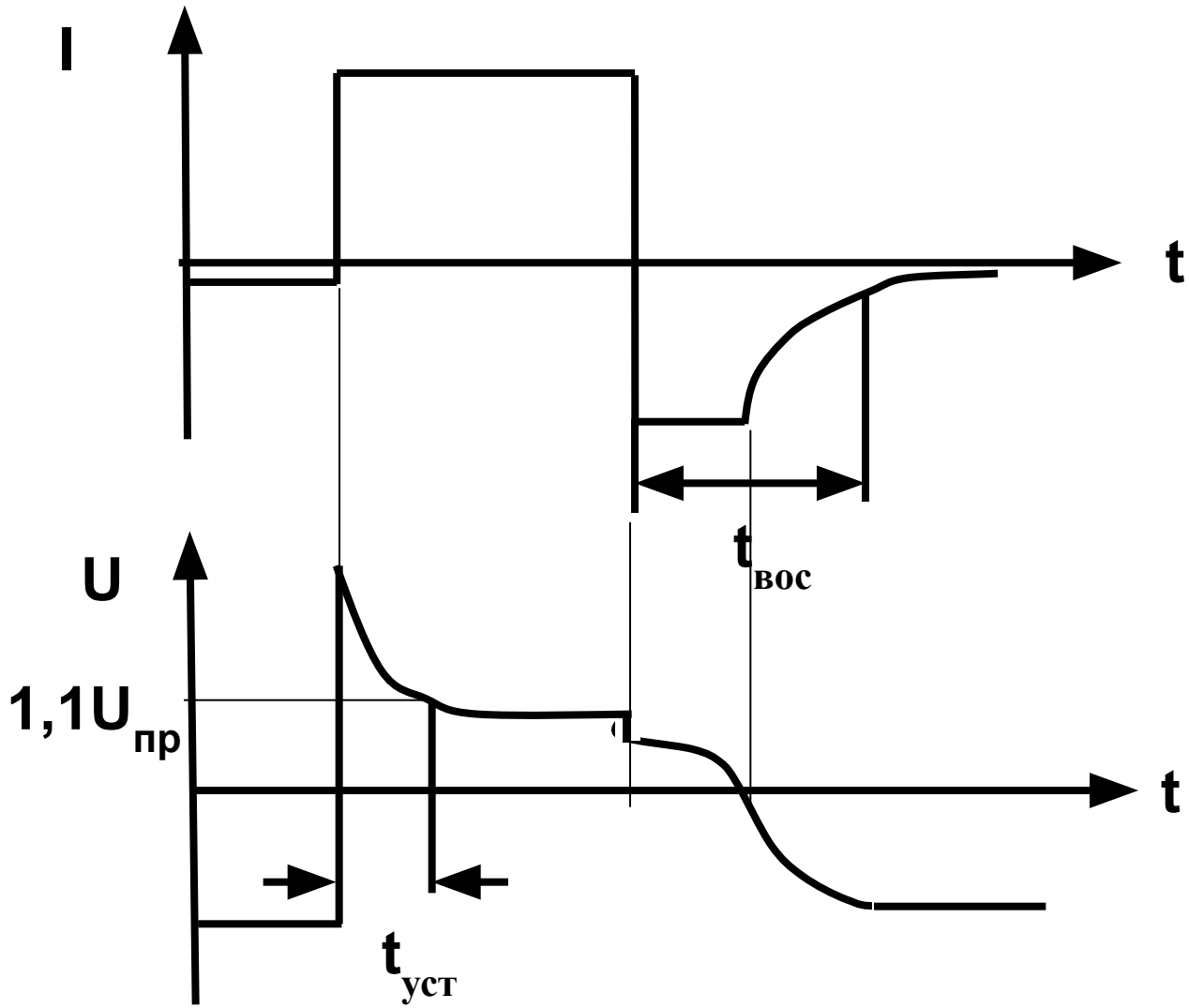
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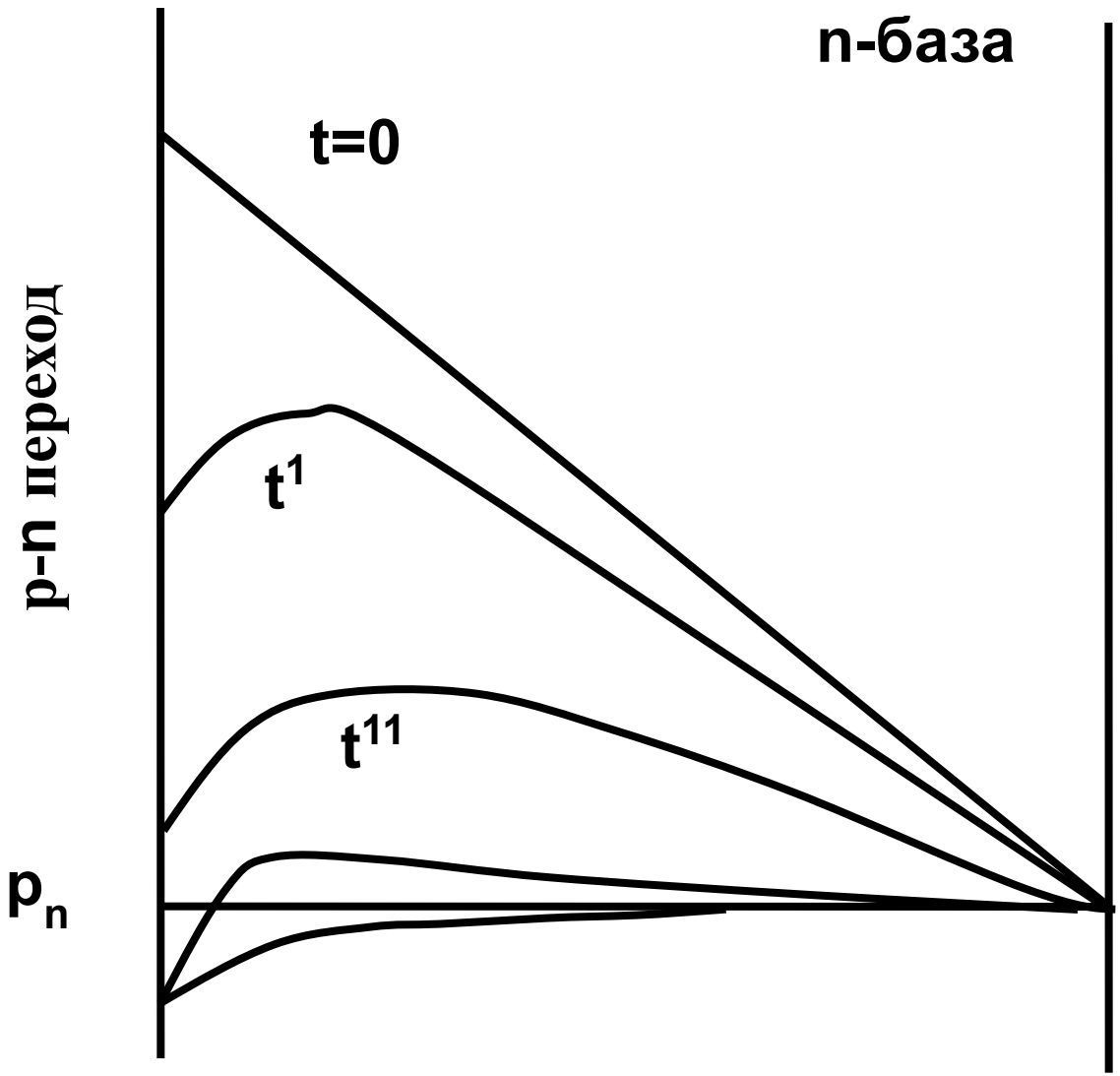
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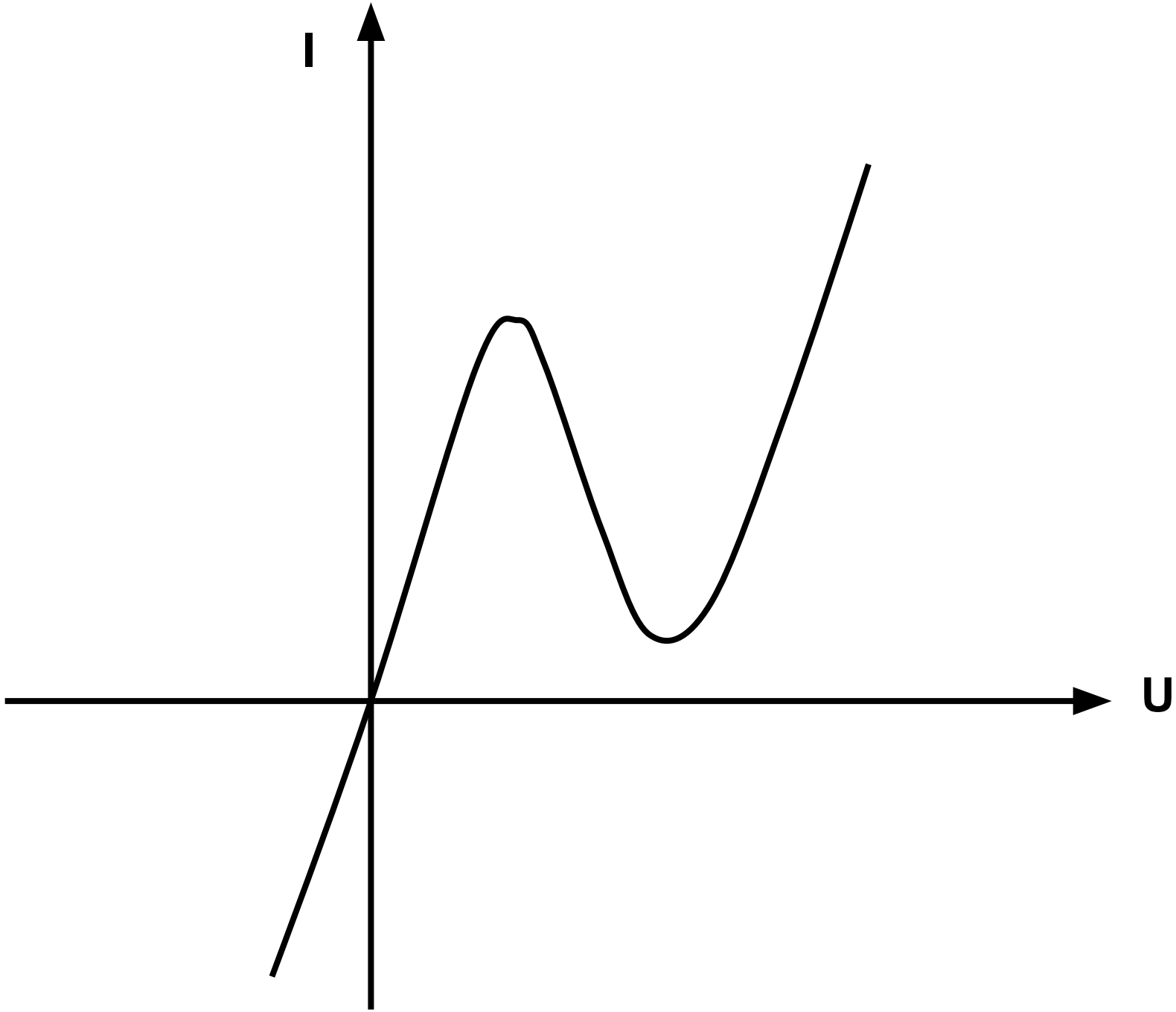
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Задание на самоподготовку

- 1. Изучить по (Л1) стр. 193-196.
- 2. Изучить по (Л9) стр. 10-17.